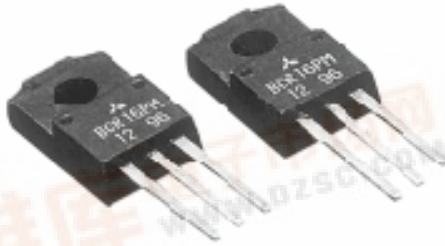


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MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

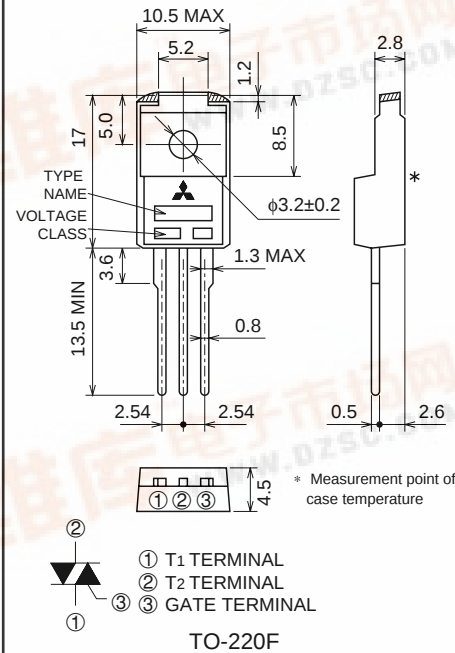
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- I_T (RMS) 16A
- V_{DRM} 400V/600V
- I_{FGT} I, I_{RGT} I, I_{RGT} III 30mA (20mA) *5
- V_{iso} 1500V
- UL Recognized: File No. E80276

OUTLINE DRAWING

Dimensions
in mm



APPLICATION

Contactless AC switches, light dimmer, electric flasher unit, hair drier, control of household equipment such as TV sets · refrigerator · washing machine · electric fan, other general purpose control applications

MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		8	12	
V_{DRM}	Repetitive peak off-state voltage *1	400	600	V
V_{DSM}	Non-repetitive peak off-state voltage *1	500	720	V

Symbol	Parameter	Conditions	Ratings	Unit
I_T (RMS)	RMS on-state current	Commercial power frequency, sine full wave 360° conduction, $T_c=71^\circ\text{C}$	16	A
I_{TSM}	Surge on-state current	60Hz sine wave 1 full cycle, peak value, non-repetitive	160	A
I^2_t	I^2_t for fusing	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current	107.5	A ² s
P_{GM}	Peak gate power dissipation		5.0	W
P_G (AV)	Average gate power dissipation		0.5	W
V_{GM}	Peak gate voltage		10	V
I_{GM}	Peak gate current		2	A
T_j	Junction temperature		-40 ~ +125	°C
T_{stg}	Storage temperature		-40 ~ +125	°C
—	Weight	Typical value	2.0	g
V_{iso}	Isolation voltage	$T_a=25^\circ\text{C}$, AC 1 minute, T1 · T2 · G terminal to case	1500	V

*1. Gate open.

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MEDIUM POWER USE
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ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IDRM	Repetitive peak off-state current	T _J =125°C, V _{DRM} applied	—	—	2.0	mA
VTM	On-state voltage	T _c =25°C, I _{TM} =25A, Instantaneous measurement	—	—	1.5	V
VFGT I	Gate trigger voltage *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	—	—	1.5	V
VRGT I			—	—	1.5	V
VRGT III			—	—	1.5	V
IFGT I	Gate trigger current *2	T _J =25°C, V _D =6V, R _L =6Ω, R _G =330Ω	—	—	30*5	mA
IRGT I			—	—	30*5	mA
IRGT III			—	—	30*5	mA
VGD	Gate non-trigger voltage	T _J =125°C, V _D =1/2V _{DRM}	0.2	—	—	V
R _{th} (j-c)	Thermal resistance	Junction to case *4	—	—	3.0	°C/W
(dv/dt) _c	Critical-rate of rise of off-state commutating voltage		*3	—	—	V/μs

*2. Measurement using the gate trigger characteristics measurement circuit.

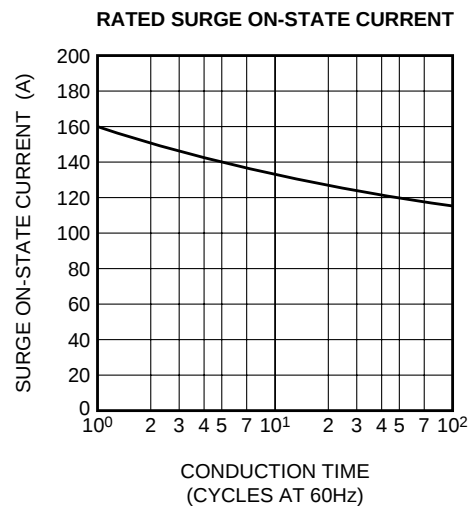
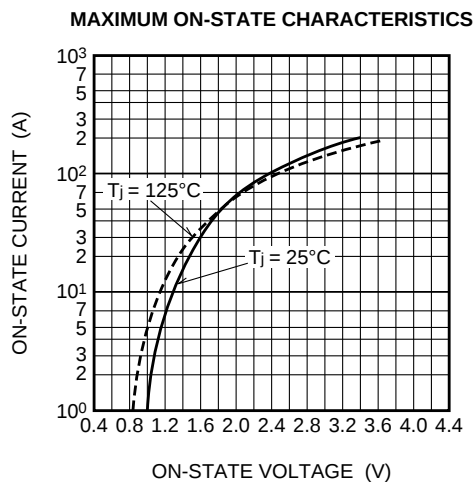
*3. The critical-rate of rise of the off-state commutating voltage is shown in the table below.

*4. The contact thermal resistance R_{th} (c-f) in case of greasing is 0.5°C/W.

*5. High sensitivity (I_{GT}≤20mA) is also available. (I_{GT} item ①)

Voltage class	V _{DRM} (V)	(dv/dt) _c			Test conditions	Commutating voltage and current waveforms (inductive load)
		Symbol	Min.	Unit		
8	400	R	—	V/μs	1. Junction temperature T _J =125°C 2. Rate of decay of on-state commutating current (di/dt) _c =-8A/ms 3. Peak off-state voltage V _D =400V	
		L	10			
12	600	R	—			
		L	10			

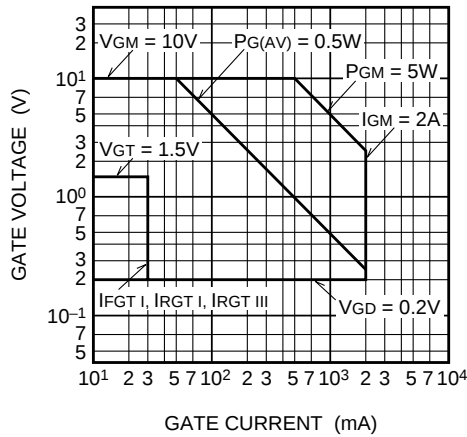
PERFORMANCE CURVES



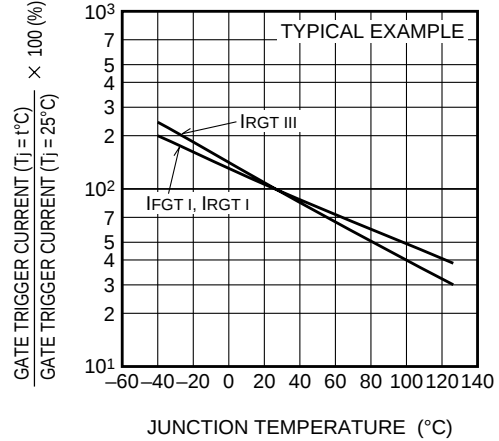
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MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE

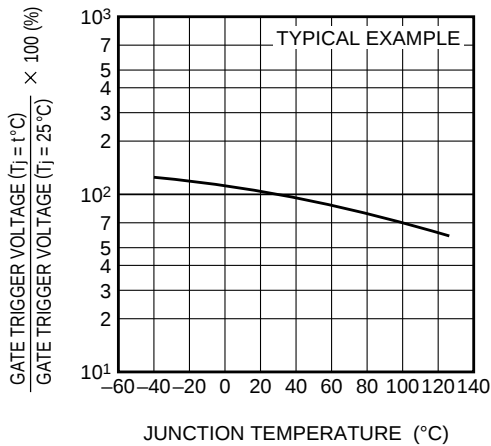
GATE CHARACTERISTICS



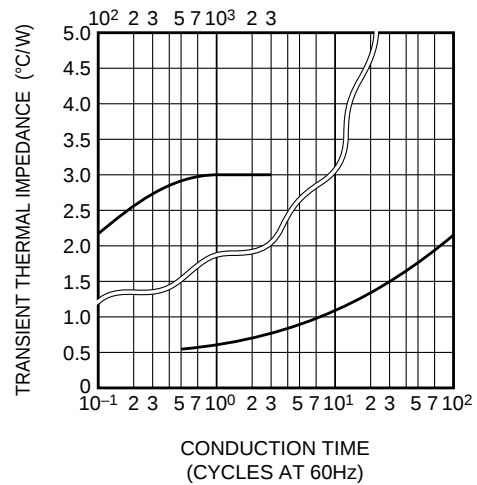
GATE TRIGGER CURRENT VS. JUNCTION TEMPERATURE



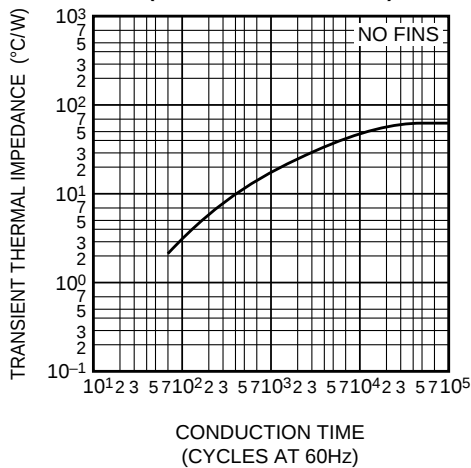
GATE TRIGGER VOLTAGE VS. JUNCTION TEMPERATURE



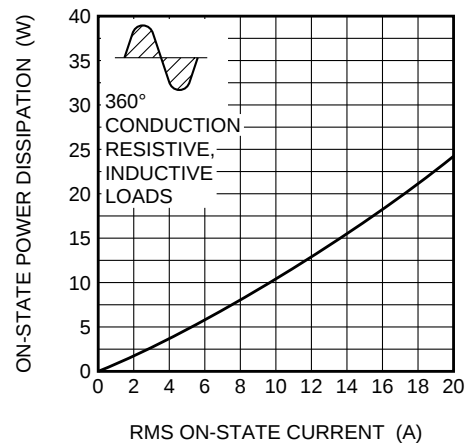
MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE)



MAXIMUM TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO AMBIENT)

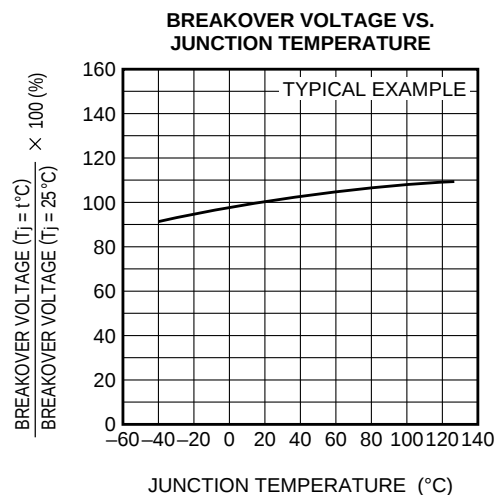
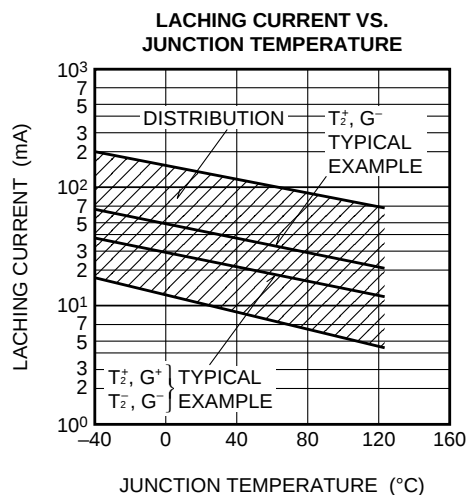
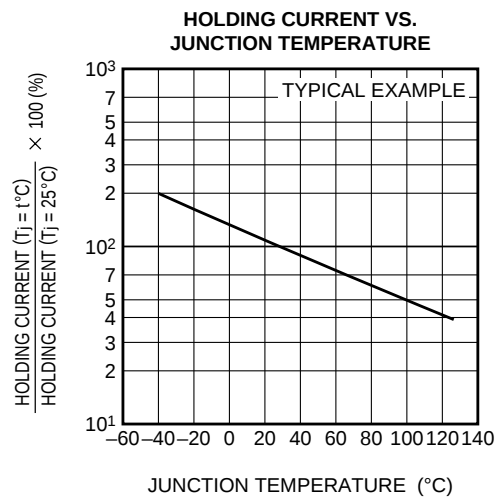
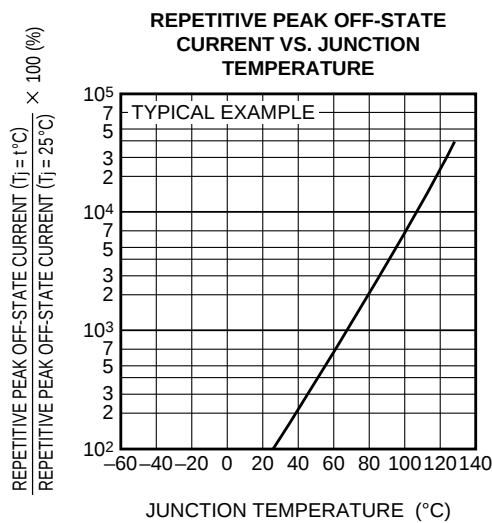
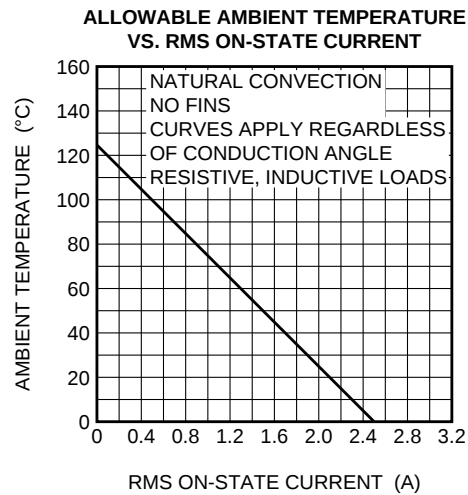
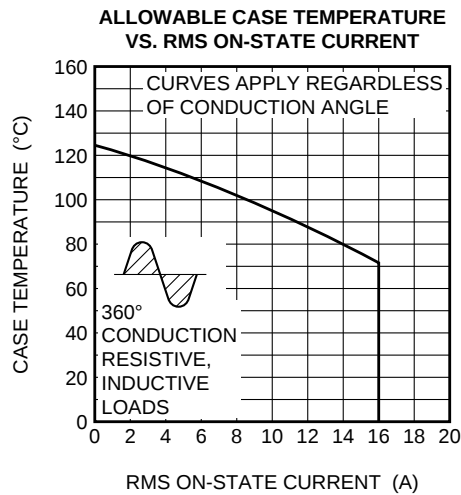


MAXIMUM ON-STATE POWER DISSIPATION



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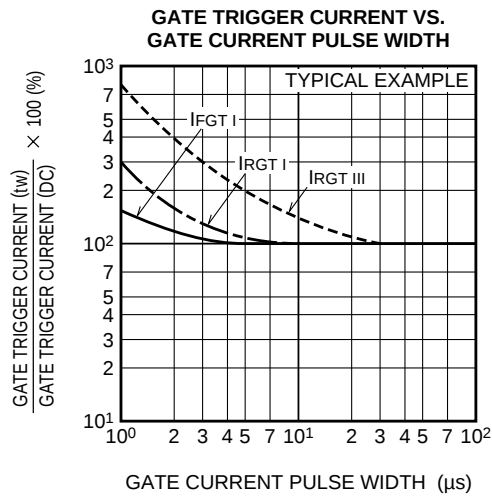
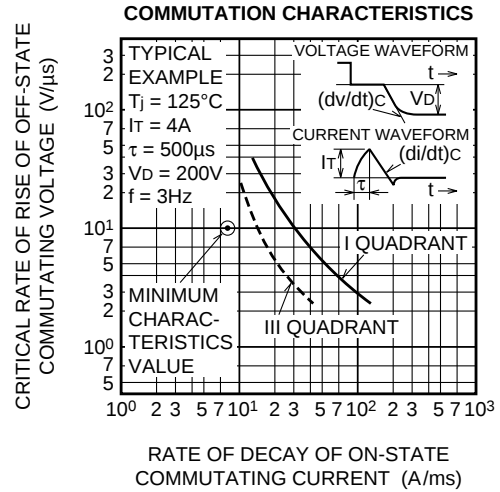
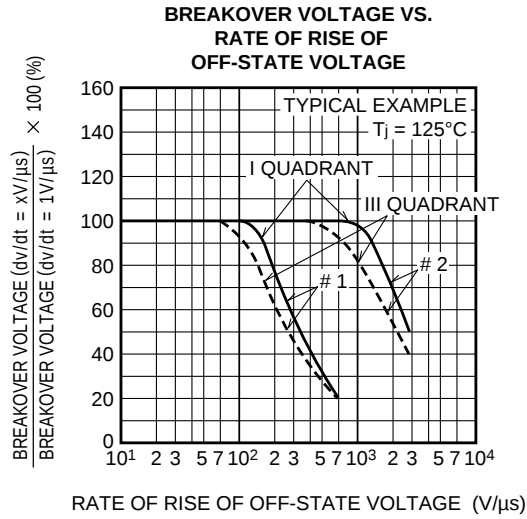
MEDIUM POWER USE
INSULATED TYPE, PLANAR PASSIVATION TYPE



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MEDIUM POWER USE

INSULATED TYPE, PLANAR PASSIVATION TYPE



GATE TRIGGER CHARACTERISTICS TEST CIRCUITS

